TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

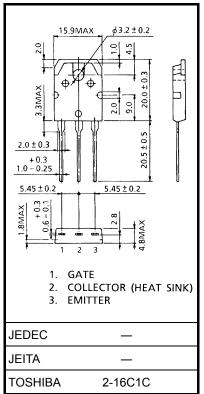
GT20J101

High Power Switching Applications

- Third-generation IGBT
- Enhancement mode type
- High speed: $t_f = 0.30 \ \mu s \ (max)$
- Low saturation voltage: VCE (sat) = 2.7 V (max)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	IC	20	A	
	1 ms	I _{CP}	40		
Collector power dissipation		Pc	130	W	
(Tc = 25°C)		ГC	150		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



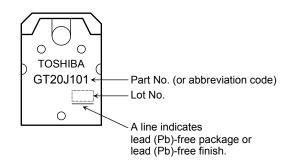
Weight: 4.6 g

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

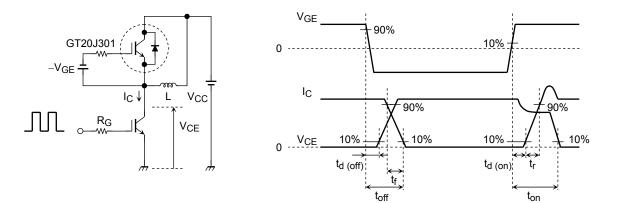


Unit: mm

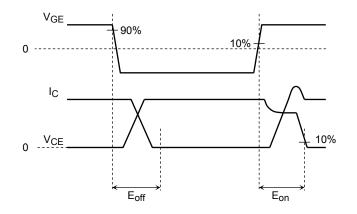
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE}=\pm 20~V,~V_{CE}=0$	_		±500	nA
Collector cut-off current		I _{CES}	$V_{CE} = 600 \text{ V}, \text{ V}_{GE} = 0$	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (OFF)}	$I_C=2\ mA,\ V_{CE}=5\ V$	5.0	_	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	$I_C = 20$ A, $V_{GE} = 15$ V		2.1	2.7	V
Input capacitance		Cies	$V_{CE}=20~V,~V_{GE}=0,~f=1~MHz$		1450	_	pF
Switching time	Rise time	tr	Inductive Load $V_{CC}=300 \text{ V}, \text{ I}_{C}=20 \text{ A}$ $V_{GG}=\pm15 \text{ V}, \text{ R}_{G}=56 \Omega$ (Note1)		0.12	_	μs
	Turn-on time	t _{on}			0.40	_	
	Fall time	t _f			0.15	0.30	
	Turn-off time	t _{off}			0.50		
Thermal resistance		R _{th (j-c)}	_	_		0.96	°C/W

Note1: Switching time measurement circuit and input/output waveforms



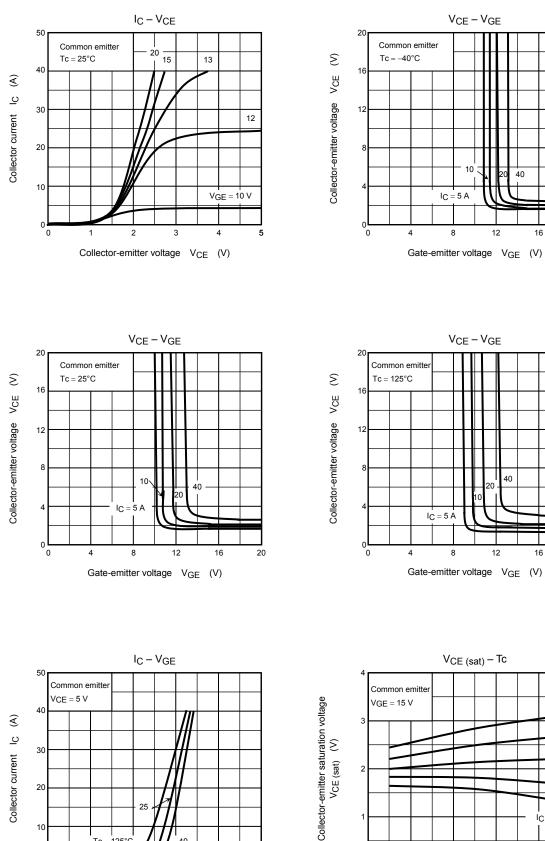
Note2: Switching loss measurement waveforms

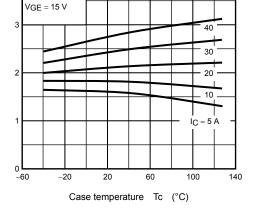


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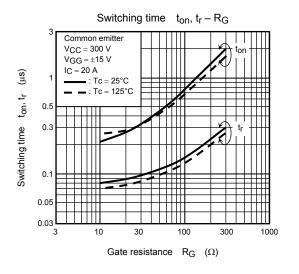
Gate-emitter voltage V_{GE} (V)

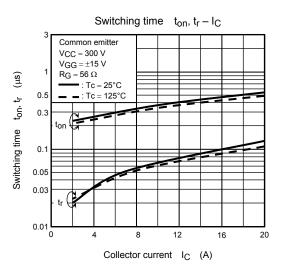
= 125°C Tc



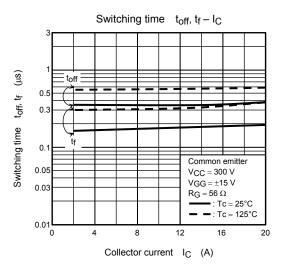


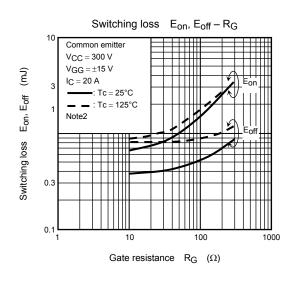
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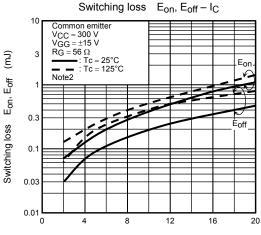




Switching time t_{off} , $t_f - R_G$ $\begin{array}{l} \text{Common emitter} \\ \text{V}_{CC} = 300 \text{ V} \end{array}$ VGG = ±15 V IC = 20 A: Tc = 25°C (ms) : Tc = 125°C tof t_{off}, tf 0.5 0.3 tf Switching time 0.1 0.05 0.03 30 300 3 10 100 1000 Gate resistance R_G (Ω)



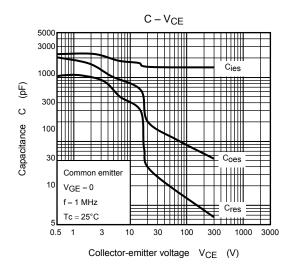


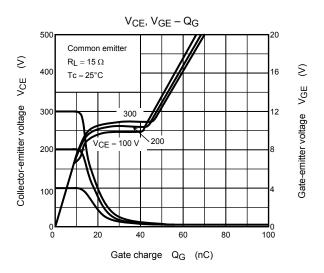


(Lm)

Switching loss

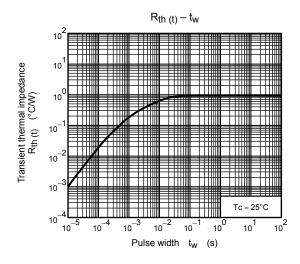
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Safe operating area 100 IC max (pulsed)* 50 11111 1111 50 μs* 100 μs 30 € IC max 10 <u>ں</u> (continuous) ms Collector current DC 3 operation Single nonrepetitive 0.5 pulse Tc = 25°C Curves must be derated 0.3 linearly with increase in temperature. 0.1 3 10 30 100 300 1000 3000 Collector-emitter voltage V_{CE} (V)

Reverse bias SOA 100 50 30 E 10 <u>ں</u> 5 Collector current 3 0.5 Tj≦ 125°C 0.3 $VGE = \pm 15 V$ $R_G = 56 \Omega$ 0.1 3000 3 10 30 100 300 1000 $Collector-emitter \ voltage \quad V_{CE} \quad (V)$



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20070701-EN

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